# E·XFL



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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	80
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100v8t7b

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

## 2 Description

The STM32F100x4, STM32F100x6, STM32F100x8 and STM32F100xB microcontrollers incorporate the high-performance ARM<sup>®</sup> Cortex<sup>®</sup>-M3 32-bit RISC core operating at a 24 MHz frequency, high-speed embedded memories (Flash memory up to 128 Kbytes and SRAM up to 8 Kbytes), and an extensive range of enhanced peripherals and I/Os connected to two APB buses. All devices offer standard communication interfaces (up to two I<sup>2</sup>Cs, two SPIs, one HDMI CEC, and up to three USARTs), one 12-bit ADC, two 12-bit DACs, up to six general-purpose 16-bit timers and an advanced-control PWM timer.

The STM32F100xx low- and medium-density devices operate in the -40 to +85 °C and -40 to +105 °C temperature ranges, from a 2.0 to 3.6 V power supply.

A comprehensive set of power-saving mode allows the design of low-power applications.

These microcontrollers include devices in three different packages ranging from 48 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included.

These features make these microcontrollers suitable for a wide range of applications such as application control and user interfaces, medical and hand-held equipment, PC and gaming peripherals, GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms, and HVACs.



Their counters can be frozen in debug mode.

#### Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as a generic 16-bit time base.

#### Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

#### Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

#### SysTick timer

This timer is dedicated for OS, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

## 2.2.16 I<sup>2</sup>C bus

The I<sup>2</sup>C bus interface can operate in multimaster and slave modes. It can support standard and fast modes.

It supports dual slave addressing (7-bit only) and both 7/10-bit addressing in master mode. A hardware CRC generation/verification is embedded. The interface can be served by DMA and it supports SM Bus 2.0/PM Bus.

## 2.2.17 Universal synchronous/asynchronous receiver transmitter (USART)

The STM32F100xx value line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3).

The available USART interfaces communicate at up to 3 Mbit/s. They provide hardware management of the CTS and RTS signals, they support IrDA SIR ENDEC, the multiprocessor communication mode, the single-wire half-duplex communication mode and have LIN Master/Slave capability.

The USART interfaces can be served by the DMA controller.



#### 2.2.23 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in noninverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- up to 10-bit output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channels' independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V<sub>REF+</sub>

Eight DAC trigger inputs are used in the STM32F100xx. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

#### 2.2.24 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 2 V <  $V_{DDA}$  < 3.6 V. The temperature sensor is internally connected to the ADC1\_IN16 input channel which is used to convert the sensor output voltage into a digital value.

### 2.2.25 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.



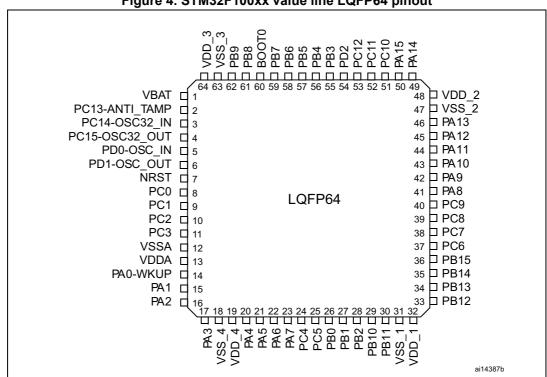
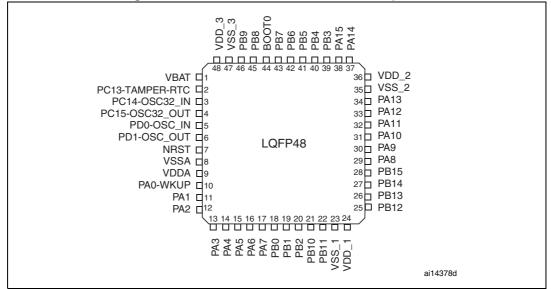


Figure 4. STM32F100xx value line LQFP64 pinout

#### Figure 5. STM32F100xx value line LQFP48 pinout





DocID16455 Rev 9

	1	2	3	4	5	6 IFBGA	7	8
A	• /PC14-, 0\&C32_lNT	, PC13-, AMPER-RT	( PB9 )	( PB4 )	(PB3)	(PA15)	(PA14)	(PA13)
в	, PC15-, OSC32_OUT	VBAT)	( PB8 )	воото	(PD2)	(PC11)	(PC10)	(PA12)
C	OSC_IN	VSS_4	( PB7 )	(PB5)	(PC12)	(PA10)	( PA9 )	(PA11)
D	OSC_OUT	VDD_4	(PB6)	,VSS_3	Vss_2	,Vss_1;	(PA8)	(PC9)
E	(NRST)	(PC1)	(PC0)	'VDD_3'	VDD_2'	, V <sub>DD_1</sub> ,	(PC7)	(PC8)
F	(VSSA)	(PC2)	(PA2 )	(PA5)	(PB0)	(PC6)	(PB15)	(PB14)
G	WREF+	PĄO-WKŲP	( PA3 )	(PA6)	(PB1)	(PB2)	(PB10)	(PB13)
н	V <sub>DDA</sub> ,	( PA1 )	(PA4)	( PA7 )	( PC4 )	(PC5)	(PB11)	(PB12)
								Al1549

Figure 6. STM32F100xx value line TFBGA64 ballout

Table 4. Low & medium-density STM32F100xx pin definitions

	Pi	ns				2)		Alternate function	s <sup>(3)(4)</sup>
LQFP100	LQFP64	TFBGA64	LQFP48	Pin name	Type <sup>(1)</sup>	I / O level <sup>(2)</sup>	Main function <sup>(3)</sup> (after reset)	Default	Remap
1	-	-	-	PE2	I/O	FT	PE2	TRACECLK	-
2	-	-	-	PE3	I/O	FT	PE3	TRACED0	-
3	-	-	-	PE4	I/O	FT	PE4	TRACED1	-
4	-	-	-	PE5	I/O	FT	PE5	TRACED2	-
5	-	-	-	PE6	I/O	FT	PE6	TRACED3	-
6	1	B2	1	V <sub>BAT</sub>	S	-	V <sub>BAT</sub>	-	-
7	2	A2	2	PC13-TAMPER-RTC <sup>(5)</sup>	I/O	-	PC13 <sup>(6)</sup>	TAMPER-RTC	-
8	3	A1	3	PC14-OSC32_IN <sup>(5)</sup>	I/O	-	PC14 <sup>(6)</sup>	OSC32_IN	-



1. I = input, O = output, S = supply, HiZ= high impedance.

- Function availability depends on the chosen device. For devices having reduced peripheral counts, it is always the lower number of peripherals that is included. For example, if a device has only one SPI, two USARTs and two timers, they will be called SPI1, USART1 & USART2 and TIM2 & TIM 3, respectively. Refer to Table 2 on page 11.
- 4. If several peripherals share the same I/O pin, to avoid conflict between these alternate functions only one peripheral should be enabled at a time through the peripheral clock enable bit (in the corresponding RCC peripheral clock enable register).
- PC13, PC14 and PC15 are supplied through the power switch and since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is restricted: the speed should not exceed 2 MHz with a maximum load of 30 pF and these IOs must *not* be used as a current source (e.g. to drive an LED).
- 6. Main function after the first backup domain power-up. Later on, it depends on the contents of the Backup registers even after reset (because these registers are not reset by the main reset). For details on how to manage these IOs, refer to the Battery backup domain and BKP register description sections in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.
- 7. The pins number 2 and 3 in the VFQFPN36 package, 5 and 6 in the LQFP48 and LQFP64 packages and C1 and C2 in the TFBGA64 package are configured as OSC\_IN/OSC\_OUT after reset, however the functionality of PD0 and PD1 can be remapped by software on these pins. For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual.
- 8. Unlike in the LQFP64 package, there is no PC3 in the TFBGA64 package. The V<sub>REF+</sub> functionality is provided instead.
- 9. I2C2 is not present on low-density value line devices.
- 10. SPI2 is not present on low-density value line devices.
- 11. TIM4 is not present on low-density value line devices.
- 12. This alternate function can be remapped by software to some other port pins (if available on the used package). For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.



<sup>2.</sup> FT= 5 V tolerant.

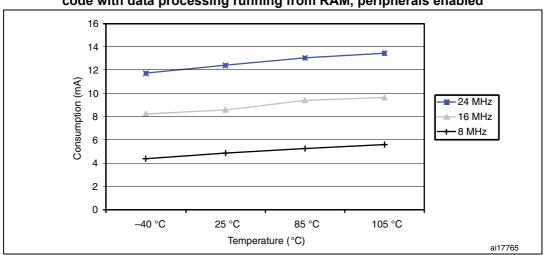


Figure 12. Maximum current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled

Figure 13. Maximum current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals disabled

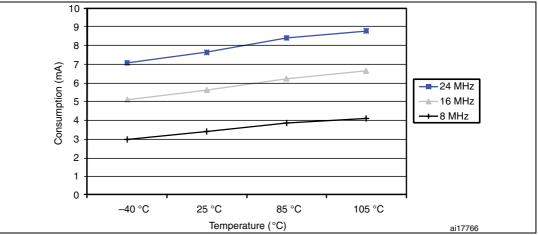


Table 14. Maximum current consumption in Sleep mode, code running from Flash or RAM

Symbol	Deremeter	Conditions	£	Ма	Unit	
	Parameter	Conditions	f <sub>HCLK</sub>	T <sub>A</sub> = 85 °C	T <sub>A</sub> = 105 °C	Unit
	Supply current in Sleep mode	External clock <sup>(2)</sup> all peripherals enabled	24 MHz	9.6	10	
			16 MHz	7.1	7.5	
			8 MHz	4.5	4.8	m 4
IDD			24 MHz	3.8	4	mA
			16 MHz	3.3	3.5	
			8 MHz	2.7	3	

1. Guaranteed by characterization, tested in production at  $V_{DD}$  max and  $f_{HCLK}$  max with peripherals enabled.

2. External clock is 8 MHz and PLL is on when  $f_{HCLK}$  > 8 MHz.



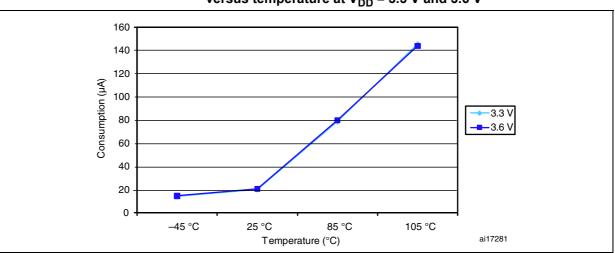
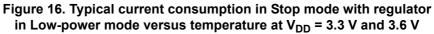
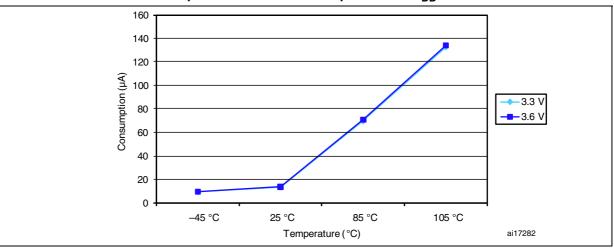


Figure 15. Typical current consumption in Stop mode with regulator in Run mode versus temperature at  $V_{DD}$  = 3.3 V and 3.6 V







		-		Typical	values <sup>(1)</sup>	
Symbol Paramete	Parameter Conditions f <sub>HCLK</sub>		f <sub>HCLK</sub>	All peripherals enabled <sup>(2)</sup>	All peripherals disabled	Unit
			24 MHz	12.8	9.3	
			16 MHz	9.3	6.6	
			8 MHz	5.1	3.9	
		Running on high-speed external clock with an	4 MHz	3.2	2.5	
	Supply current in Run mode	8 MHz crystal <sup>(3)</sup>	2 MHz	2.1	1.75	
			1 MHz	1.55	1.4	
			500 kHz	1.3	1.2	mA
			125 kHz	1.1	1.05	
I <sub>DD</sub>			24 MHz	12.2	8.6	
			16 MHz	8.5	6	
			8 MHz	4.6	3.3	
		Running on high-speed	4 MHz	2.6	1.9	
		internal RC (HSI)	2 MHz	1.5	1.15	
			1 MHz	0.9	0.8	
			500 kHz	0.65	0.6	
				0.45	0.43	

Table 16. Typical current consumption in Run mode, code with data processingrunning from Flash

1. Typical values are measures at  $T_A = 25$  °C,  $V_{DD} = 3.3$  V.

2. Add an additional power consumption of 0.8 mA for the ADC and of 0.5 mA for the DAC analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC\_CR2 register).

3. An 8 MHz crystal is used as the external clock source. The AHB prescaler is used to reduce the frequency when  $f_{HCLK} < 8$  MHz, the PLL is used when  $f_{HCLK} > 8$  MHz.



				Typical	values <sup>(1)</sup>	
Symbol	Parameter	Conditions	f <sub>HCLK</sub>	All peripherals enabled <sup>(2)</sup>	All peripherals disabled	Unit
			24 MHz	7.3	2.6	
			16 MHz	5.2	2	
			8 MHz	2.8	1.3	
		Running on high-speed external clock with an	4 MHz	2	1.1	
	Supply	8 MHz crystal <sup>(3)</sup>	2 MHz	1.5	1.1	
			1 MHz	1.25	1	mA
			500 kHz	1.1	1	
1	Supply current in		125 kHz	1.05	0.95	
I <sub>DD</sub>	Sleep mode		24 MHz	6.65	1.9	
	mode		16 MHz	4.5	1.4	
			8 MHz	2.2	0.7	
		Running on high-speed	4 MHz	1.35	0.55	
		internal RC (HSI)	2 MHz	0.85	0.45	
			1 MHz	0.6	0.41	-
			500 kHz	0.5	0.39	
			125 kHz	0.4	0.37	

Table 17. Typical current consumption in Sleep mode, code running from Flash or RAM

1. Typical values are measures at  $T_A$  = 25 °C,  $V_{DD}$  = 3.3 V.

2. Add an additional power consumption of 0.8 mA for the ADC and of 0.5 mA for the DAC analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC\_CR2 register).

3. An 8 MHz crystal is used as the external clock source. The AHB prescaler is used to reduce the frequency when  $f_{HCLK} > 8$  MHz, the PLL is used when  $f_{HCLK} > 8$  MHz.

## On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 18*. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at  $V_{DD}$  or  $V_{SS}$  (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- ambient operating temperature and V<sub>DD</sub> supply voltage conditions summarized in Table 5.



## 5.3.6 External clock source characteristics

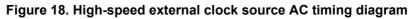
### High-speed external user clock generated from an external source

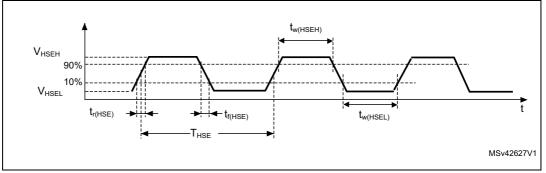
The characteristics given in *Table 19* result from tests performed using an high-speed external clock source, and under the ambient temperature and supply voltage conditions summarized in *Table 8*.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f <sub>HSE_ext</sub>	User external clock source frequency <sup>(1)</sup>		1	8	24	MHz
V <sub>HSEH</sub>	OSC_IN input pin high level voltage <sup>(1)</sup>		0.7V <sub>DD</sub>	-	V <sub>DD</sub>	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage <sup>(1)</sup>			-	0.3V <sub>DD</sub>	v
t <sub>w(HSEH)</sub> t <sub>w(HSEL)</sub>	OSC_IN high or low time <sup>(1)</sup>		5	-	-	20
t <sub>r(HSE)</sub> t <sub>f(HSE)</sub>	OSC_IN rise or fall time <sup>(1)</sup>	- V <sub>SS</sub> low time <sup>(1)</sup> all time <sup>(1)</sup>		-	20	ns
C <sub>in(HSE)</sub>	OSC_IN input capacitance <sup>(1)</sup>	-	-	5	-	pF
DuCy <sub>(HSE)</sub>	Duty cycle <sup>(1)</sup>	-	45	-	55	%
ΙL	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA

Table 19. High-speed external user clock characteristics

1. Guaranteed by design.







#### Low-speed internal (LSI) RC oscillator

Table 24. LSI oso	illator characteristics <sup>(1)</sup>	)
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Symbol	Parameter	Min	Тур	Max	Unit
f <sub>LSI</sub>	Frequency	30	40	60	kHz
$\Delta f_{LSI(T)}$	Temperature-related frequency drift <sup>(2)</sup>	-9	-	9	%
t <sub>su(LSI)</sub> <sup>(3)</sup>	LSI oscillator startup time	-	-	85	μs
I <sub>DD(LSI)</sub> <sup>(3)</sup>	LSI oscillator power consumption	-	0.65	1.2	μA

1.  $V_{DD}$  = 3 V,  $T_A$  = -40 to 105 °C °C unless otherwise specified.

2. Guaranteed by characterization results.

3. Guaranteed by design.

#### Wakeup time from low-power mode

The wakeup times given in *Table 25* are measured on a wakeup phase with an 8-MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 8*.

Symbol	Parameter	Тур	Unit
t <sub>WUSLEEP</sub> <sup>(1)</sup>	Wakeup from Sleep mode	1.8	μs
t <sub>WUSTOP</sub> <sup>(1)</sup>	Wakeup from Stop mode (regulator in run mode)	3.6	
'WUSTOP'	Wakeup from Stop mode (regulator in low-power mode)	5.4	μs
t <sub>WUSTDBY</sub> <sup>(1)</sup>	Wakeup from Standby mode	50	μs

Table 25. Low-power mode wakeup timings

1. The wakeup times are measured from the wakeup event to the point at which the user application code reads the first instruction.



## 5.3.13 I/O port characteristics

#### General input/output characteristics

Unless otherwise specified, the parameters given in *Table 34* are derived from tests performed under the conditions summarized in *Table 8*. All I/Os are CMOS and TTL compliant.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
M	Standard I/O input low level voltage		-0.3	-	0.28*(V <sub>DD</sub> -2 V)+0.8 V	
V <sub>IL</sub>	I/O FT <sup>(1)</sup> input low level voltage	-	-0.3	-	0.32*(V <sub>DD</sub> -2 V)+0.75 V	
	Standard I/O input high level voltage		0.41*(V <sub>DD</sub> -2 V) +1.3 V	-	V <sub>DD</sub> +0.3	V
V <sub>IH</sub>	I/O FT <sup>(1)</sup> input high	$V_{DD} > 2 V$	0.42*(\/2\+1.\/		0.28*(V <sub>DD</sub> -2 V)+0.8 V 0.32*(V <sub>DD</sub> -2 V)+0.75 V	
	level voltage	V <sub>DD</sub> ≤2 V	0.42*(V <sub>DD</sub> –2)+1 V	-	5.2	
V <sub>hys</sub>	Standard I/O Schmitt trigger voltage hysteresis <sup>(2)</sup>	-	200	-	-	mV
	I/O FT Schmitt trigger voltage hysteresis <sup>(2)</sup>		5% V <sub>DD</sub> <sup>(3)</sup>	-	-	mV
1	Input leakage	V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> Standard I/Os	-	-	±1	
l <sub>lkg</sub>	current <sup>(4)</sup>	V <sub>IN</sub> = 5 V I/O FT	-	-	3	μA
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(5)</sup>	$V_{IN} = V_{SS}$	30	40	50	kΩ
R <sub>PD</sub>	Weak pull-down equivalent resistor <sup>(5)</sup>	$V_{IN} = V_{DD}$	30	40	50	kΩ
CIO	I/O pin capacitance	-	-	5	-	pF

1. FT = 5V tolerant. To sustain a voltage higher than V<sub>DD</sub>+0.3 the internal pull-up/pull-down resistors must be disabled.

2. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by design.

- 3. With a minimum of 100 mV.
- 4. Leakage could be higher than max. if negative current is injected on adjacent pins.
- 5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimum (~10% order).

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 22* and *Figure 23* for standard I/Os, and in *Figure 24* and *Figure 25* for 5 V tolerant I/Os.



T <sub>s</sub> (cycles)	t <sub>S</sub> (μs)	R <sub>AIN</sub> max (kΩ)
1.5	0.125	0.4
7.5	0.625	5.9
13.5	1.125	11.4
28.5	2.375	25.2
41.5	3.45	37.2
55.5	4.625	50
71.5	5.96	NA
239.5	20	NA

#### Table 43. $R_{AIN}$ max for $f_{ADC} = 12 \text{ MHz}^{(1)}$

1. Guaranteed by design.

Symbol	Parameter	Test conditions	Тур	Мах	Unit
ET	Total unadjusted error	$f_{PCLK2} = 24 \text{ MHz},$	±1.3	±2.2	
EO	Offset error	f <sub>ADC</sub> = 12 MHz, R <sub>AIN</sub> < 10 kΩ V <sub>DDA</sub> = 3 V to 3.6 V	±1	±1.5	
EG	Gain error	$V_{\text{REF+}} = V_{\text{DDA}}$	±0.5	±1.5	LSB
ED	Differential linearity error	T <sub>A</sub> = 25 °C	±0.7	±1	
EL	Integral linearity error	Measurements made after ADC calibration	±0.8	±1.5	

Table 44. ADC accuracy - limited test conditions <sup>(1)(2)</sup>
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1. ADC DC accuracy values are measured after internal calibration.

2. Guaranteed by characterization results.

Table	45. A	DC	accuracy <sup>(1) (2) (3)</sup>
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Symbol	Parameter	Test conditions	Тур	Max	Unit
ET	Total unadjusted error	f <sub>PCLK2</sub> = 24 MHz,	±2	±5	
EO	Offset error	$f_{ADC}$ = 12 MHz, $R_{AIN}$ < 10 kΩ	±1.5	±2.5	
EG	Gain error	$V_{DDA} = 2.4 V$ to 3.6 V T <sub>A =</sub> Full operating range	±1.5	±3	LSB
ED	Differential linearity error	Measurements made after	±1	±2	
EL	Integral linearity error	ADC calibration	±1.5	±3	

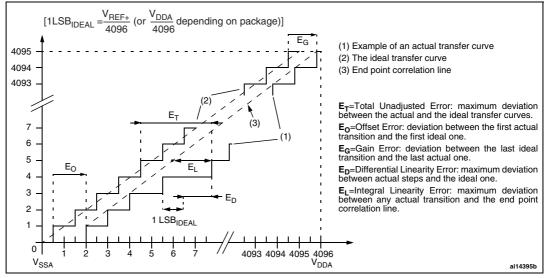
1. ADC DC accuracy values are measured after internal calibration.

2. Better performance could be achieved in restricted  $V_{DD}$ , frequency,  $V_{REF}$  and temperature ranges.

3. Guaranteed by characterization results.

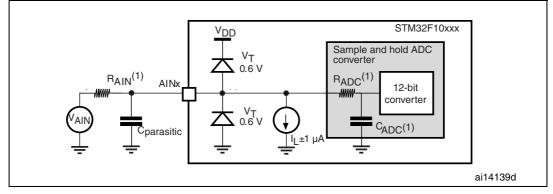
Note:ADC accuracy vs. negative injection current: Injecting a negative current on any analog<br/>input pins should be avoided as this significantly reduces the accuracy of the conversion<br/>being performed on another analog input. It is recommended to add a Schottky diode (pin to<br/>ground) to analog pins which may potentially inject negative currents.<br/>Any positive injection current within the limits specified for I<sub>INJ(PIN)</sub> and ΣI<sub>INJ(PIN)</sub> in<br/>Section 5.3.12 does not affect the ADC accuracy.





#### Figure 32. ADC accuracy characteristics

#### Figure 33. Typical connection diagram using the ADC



1. Refer to Table 42 for the values of  $R_{AIN}$ ,  $R_{ADC}$  and  $C_{ADC}$ .

 C<sub>parasitic</sub> represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C<sub>parasitic</sub> value will downgrade conversion accuracy. To remedy this, f<sub>ADC</sub> should be reduced.

#### General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 34* or *Figure 35*, depending on whether  $V_{REF+}$  is connected to  $V_{DDA}$  or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.



## 5.3.18 DAC electrical specifications

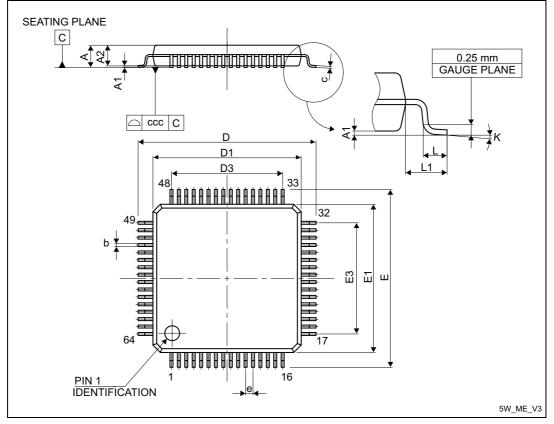
Symbol	Parameter	Parameter Min Typ		Max <sup>(1)</sup>	Unit	Comments
V <sub>DDA</sub>	Analog supply voltage	2.4	-	3.6	V	-
$V_{REF^+}$	Reference supply voltage		-	3.6	V	V <sub>REF+</sub> must always be below V <sub>DDA</sub>
V <sub>SSA</sub>	Ground	0	-	0	V	-
R <sub>LOAD</sub> <sup>(2)</sup>	Resistive load with buffer ON	5	-	-	kΩ	-
R <sub>0</sub> <sup>(1)</sup>	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and $V_{SS}$ to have a 1% accuracy is 1.5 M $\Omega$
C <sub>LOAD</sub> <sup>(1)</sup>	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min <sup>(1)</sup>	Lower DAC_OUT voltage with buffer ON	0.2	-	-	v	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at
DAC_OUT max <sup>(1)</sup>	Higher DAC_OUT voltage with buffer ON	-	-	V <sub>DDA</sub> - 0.2	V	$V_{REF+} = 3.6 V \text{ and } (0x155) \text{ and} (0xEAB) \text{ at } V_{REF+} = 2.4 V$
DAC_OUT min <sup>(1)</sup>	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output
DAC_OUT max <sup>(1)</sup>	Higher DAC_OUT voltage with buffer OFF	-	-	V <sub>REF+</sub> – 1LSB	V	excursion of the DAC.
I <sub>DDVREF+</sub>	DAC DC current consumption in quiescent mode (Standby mode)	-	-	220	μA	With no load, worst code (0xF1C) at V <sub>REF+</sub> = 3.6 V in terms of DC consumption on the inputs
		-	-	380	μA	With no load, middle code (0x800) on the inputs
I <sub>DDA</sub>	DAC DC current consumption in quiescent mode (Standby mode)		-	480	μA	With no load, worst code (0xF1C) at $V_{REF+}$ = 3.6 V in terms of DC consumption on the inputs
DNL <sup>(1)</sup>	Differential non linearity Difference between two	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
	consecutive code-1LSB)	-	-	±2	LSB	Given for the DAC in 12-bit configuration
њи (1)	Integral non linearity (difference between measured value at	-	-	±1	LSB	Given for the DAC in 10-bit configuration
INL <sup>(1)</sup>	Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±4	LSB	Given for the DAC in 12-bit configuration

#### Table 46. DAC characteristics



## 6.2 LQFP64 package information

Figure 40.LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline



1. Drawing is not in scale.

Table 49. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package
mechanical data

Current e l		millimeters				
Symbol	Min	Тур	Мах	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-

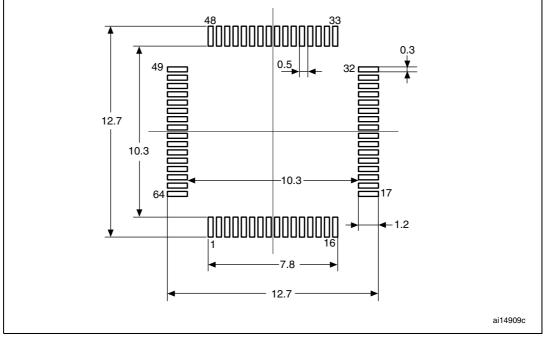


Or week all		millimeters			inches <sup>(1)</sup>	
Symbol	Min Typ Max		Min	Max		
е	-	0.500	-	-	0.0197	-
К	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
CCC	-	-	0.080	-	-	0.0031

## Table 49. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat packagemechanical data (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.





1. Dimensions are in millimeters.



Date	Revision	Changes
		Revision history corrected.
		Updated Table 6: Current characteristics Values and note updated in Table 16: Typical current consumption in Run mode, code with data processing running from Flash and Table 17: Typical current consumption in Sleep mode, code running from Flash or RAM.
30-Mar-2010	3	Updated Table 15: Typical and maximum current consumptions in Stop and Standby modes Added Figure 14: Typical current consumption on VBAT with RTC on vs. temperature at different VBAT values Typical consumption for ADC1 corrected in Table 18: Peripheral
		<i>current consumption.</i> <i>Maximum current consumption</i> and <i>Typical current consumption</i> : frequency conditions corrected. <i>Output driving current</i> corrected. Updated <i>Table 30: EMI characteristics</i> f <sub>ADC</sub> max corrected in <i>Table 42: ADC characteristics</i> . Small text changes.
06-May-2010	4	Updated Table 31: ESD absolute maximum ratings on page 55 and Table 32: Electrical sensitivities on page 56 Updated Table 44: ADC accuracy - limited test conditions on page 70 and Table 45: ADC accuracy on page 70
12-Jul-2010	5	Updated Table 24: LSI oscillator characteristics on page 51 Updated Table 44: ADC accuracy - limited test conditions on page 70 and Table 45: ADC accuracy on page 70
04-Apr-2011	6	Updated <i>Figure 2: Clock tree</i> to add FLITF clock Updated footnotes below <i>Table 5: Voltage characteristics on page 33</i> and <i>Table 6: Current characteristics on page 34</i> Updated tw min in <i>Table 19: High-speed external user clock</i> <i>characteristics on page 46</i> Updated startup time in <i>Table 22: LSE oscillator characteristics (fLSE</i> = 32.768 kHz) on page 49 Updated <i>Table 23: HSI oscillator characteristics on page 50</i> Added Section 5.3.12: I/O current injection characteristics on page 56 Updated <i>Table 34: I/O static characteristics on page 57</i> Corrected TTL and CMOS designations in <i>Table 35: Output voltage</i> <i>characteristics on page 60</i> Removed note on remapped characteristics from <i>Table 41: SPI</i> <i>characteristics on page 66</i>

#### Table 55. Document revision history (continued)





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